

Silicon PNP Power Transistors

2SB1367

DESCRIPTION

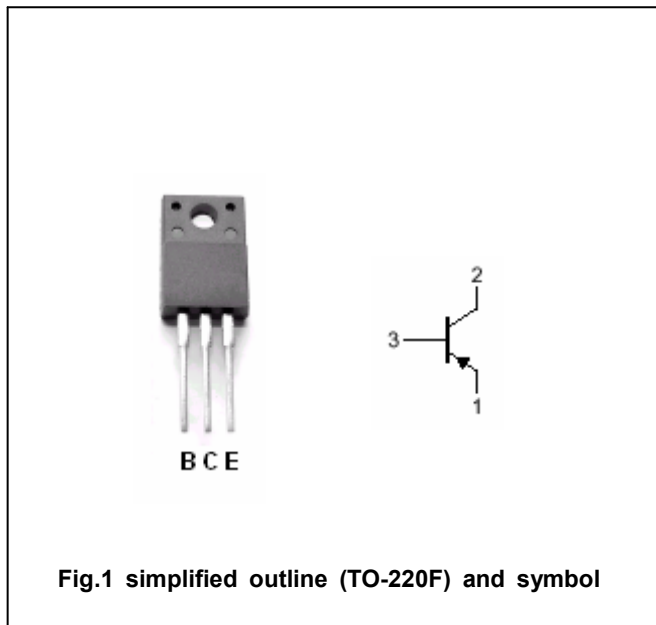
- With TO-220F package
- Complement to type 2SD2059
- Low collector saturation voltage:
 $V_{CE(sat)} = -2.0V(\text{Max})$ at $I_C = -4A, I_B = -0.4A$
- Collector power dissipation:
 $P_C = 30W(T_C = 25^\circ\text{C})$

APPLICATIONS

- With general purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
I_B	Base current		-0.5	A
P_C	Collector dissipation	$T_C = 25^\circ\text{C}$	30	W
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA ; I _B =0	-100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-4A ; I _B =-0.4A			-2.0	V
V _{BE}	Base-emitter on voltage	I _C =-4A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V ; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-1.0	mA
h _{FE-1}	DC current gain	I _C =-1A ; V _{CE} =-5V	40		240	
h _{FE-2}	DC current gain	I _C =-4A ; V _{CE} =-5V	20			
f _T	Transition frequency	I _C =-1A ; V _{CE} =-5V		5.0		MHz
C _{OB}	Collector output capacitance	f=1MHz ; V _{CB} =-10V		270		pF

◆ h_{FE-1} Classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

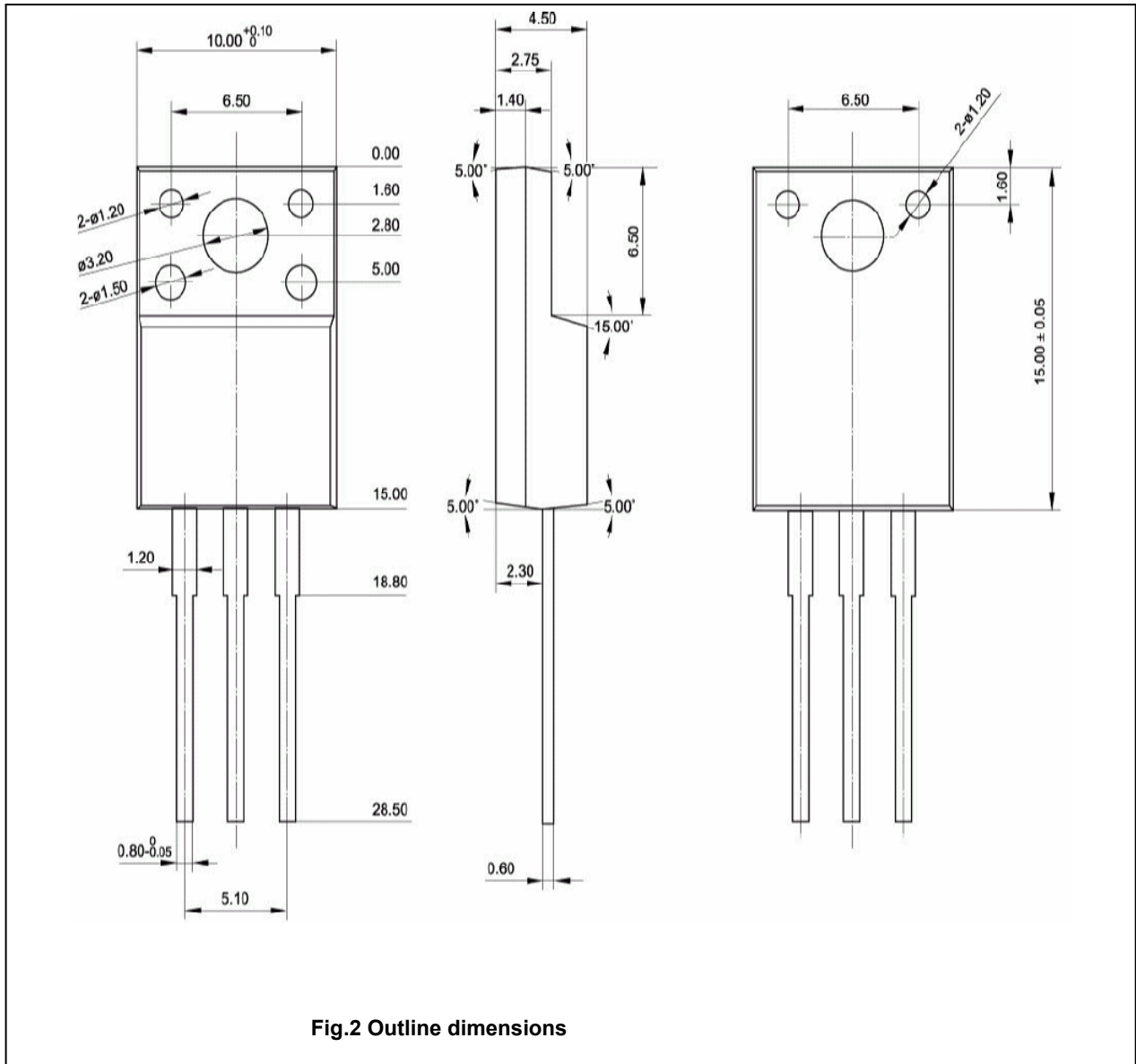


Fig.2 Outline dimensions

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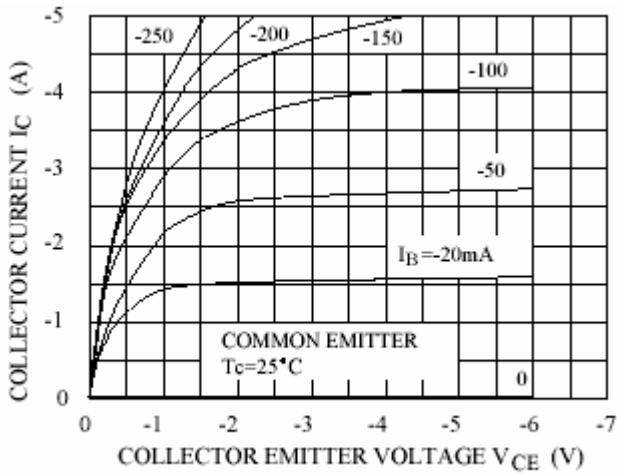


Fig.3 Static Characteristic

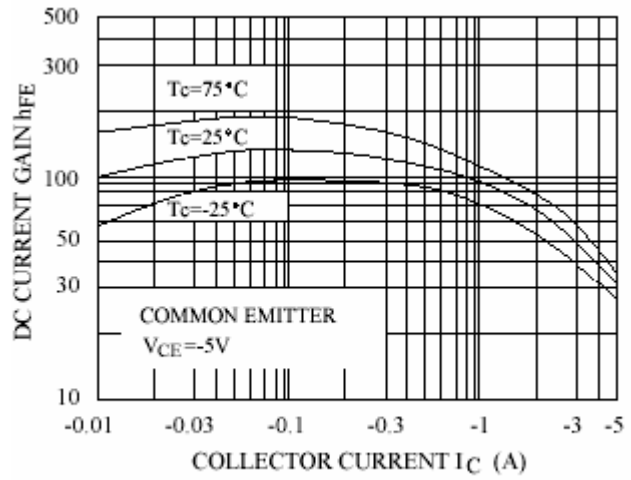


Fig.4 DC current Gain

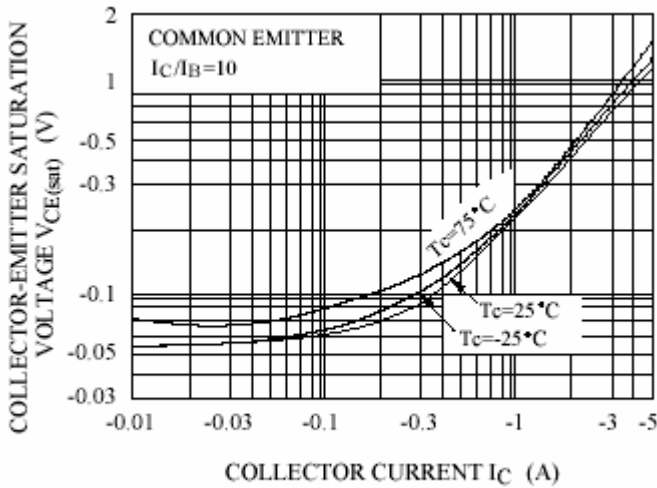


Fig.5 Collector-Emitter Saturation Voltage

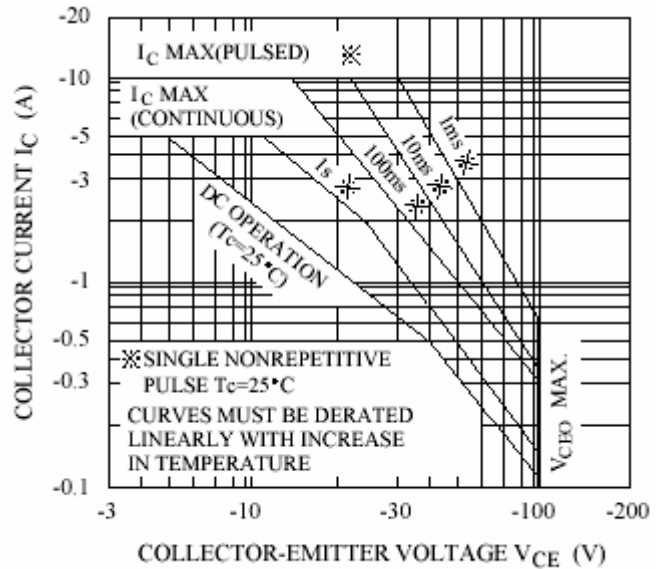


Fig.6 Safe Operating Area